

Pin Assignments





SINGLE-POLE DOUBLE-THROW ANALOG SWITCH

Description

The 74LVC1G3157 is a single-pole, double-throw analog switch. The device is designed for operation with a power supply range of 1.65V to 5.5V. The bidirectional switch can handle signal amplitudes between Vcc and Ground. The OFF state impedance of the switch is typically $50M\Omega$ while the ON state is typically 6Ω .

Features

- Wide Supply Voltage Range from 1.65 to 5.5V
- Control Pin Includes Hysteresis Allowing for Slower Input Rise
 and Fall Times
- CMOS Low Power Consumption
- Very Low ON-State Resistance
 - 7.5 Ω (typical) at V_{CC} = 2.7V
 - 6.5 Ω (typical) at V_{CC} = 3.3V
 - 6 Ω (typical) at V_{CC} = 4.5V
- Break Before Make Switching
- Control Input accepts up to 5.5V Regardless of Vcc.
- Direct Interface with TTL Levels when V_{CC} = 3.3V
- ESD Protection Tested per JESD 22
 - Exceeds 200-V Machine Model (A115)
 - Exceeds 2,000-V Human Body Model (A114)
 - Exceeds 1,000-V Charged Device Model (C101)
- Latch-Up Exceeds 100mA per JESD 78, Class I
- Range of Package Options
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

(Top View) B1 1 6 Select





Packages not to scale

Applications

- Multiplexing of Analog Signals
- Multiplexing of Digital Signals
- Wide array of products such as:
 - Tablets, E-readers, Wearables
 - Cell Phones, Personal Navigation / GPS
 - MP3 Players, Cameras, Video Recorders
 - Computer Peripherals, Hard Drives, CD/DVD ROMs
 - TV, DVD, DVR, Set Top Boxes
 - PCs, Networking, Notebooks, Netbooks, PDAs
- Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.





74LVC1G3157

Ordering Information (Note 4)



Dovico	Package	Package	Package	7" Tape and Reel (Note 6)			
Device	Code	(Note 5)	Size	Quantity	Part Number Suffix		
74LVC1G3157DW-7	DW	SOT363	2.0mm x 2.0mm x 1.1mm 0.65 mm lead pitch	3,000/Tape & Reel	-7		
74LVC1G3157FZ4-7	FZ4	X2-DFN1410-6	1.4mm x 1.0mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7		

Notes: 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

5. Pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

6. The taping orientation is located on our website at https://www.diodes.com/assets/Datasheets/ap02007.pdf.

Pin Descriptions

Function Table

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Pin Name	Description	
B1	Selectable Data I/0	
GND	Ground	
B0	Selectable Data I/0	
А	Common Data I/0	
V _{cc}	Supply Voltage	
Select	Selection Pin	

Status B1 connected to A;

B0 high impedance B0 connected to A;

B1 high impedance

Logic Diagram



Simplified Schematic

-		
	P4 1	
	ВІ —	•
	Select <u>6</u>	┍҄Ӯ━━
	B0 <u></u>	╡

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<u>4</u> A





Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
ESD MM	Machine Model ESD Protection	200	V
V _{cc}	Supply Voltage Range	-0.5 to 6.5	V
V _{IN}	Input Voltage Range Applicable to Select Pin	-0.5 to 6.5	V
V _{SW}	Voltage Range Applicable to B0, B1, and A Pins	-0.5 to V _{cc} +0.5	V
I _{IK}	Input Clamp Current VI<0 Applicable to Select Pin	-50	mA
I _{IO}	Continuous Current Applicable to B0,B1, and A Pins	±50	mA
$I_{CC, I_{GND}}$	Continuous current through V_{CC} or GND	±100	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Note: 7. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Recommended Operating Conditions

Symbol		Parameter	Min	Мах	Unit	
V _{cc}	Operating Voltage	Operating	1.65	5.5	V	
V _{IN}	Select Input Voltage		0	5.5	V	
V _{SW}	Switch Voltage (applicable to pir	-0.2	V _{cc}	V		
	Input Transition Rise or Fall	ut Transition Rise or Fall V _{CC} = 1.65 to 2.7V		20		
Δτ/Δν	Rate – Select Pin	$V_{CC} = 2.7 V$ to 5.5 V	-	10	ns/V	
T _A	Operating Free-Air Temperature	-	-40	+125	°C	





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Electrical Characteristics (All typical values are at, T_J = +25°C)

				TA	= -40 to +85°	°C	T _A = -40	to +125°C	
Symbol	Parameter	Test Condition	V _{cc} (V)	Min	Typical (Note 8)	Max	Min	Мах	Unit
			1.65 to 1.95	0.65V _{CC}	-	-	$0.65V_{CC}$	-	
Ň	High Level		2.3 to 2.7	1.7	-	-	1.7	-	v
VIH	Select Pin	-	3 to 3.6	2.0	-	-	2.0	-	V
			4.5 to 5.5	0.7V _{CC}	-	-	$0.7V_{CC}$	-	
			1.65 to 1.95	-	-	$0.35V_{CC}$	-	$0.35V_{CC}$	
N	Low Level		2.3 to 2.7	-	-	0.7	-	0.7	
VIL	Select Pin	-	3 to 3.6	-	-	0.8	-	0.8	V
			4.5 to 5.5	-	-	$0.3V_{CC}$	-	0.3V _{CC}	
I _{IN}	Input Leakage Current Select Pin	$0 \le \text{Select} \le 5.5\text{V}$	0 to 5.5	-	±0.05	±1	-	±10	μA
I _{S(OFF)}	OFF State Leakage Current	0V ≤ A, B _n ≤ V _{CC} Figure 1	1.65 to 5.5	-	±0.05	±1	-	±10	μA
I _{S(ON)}	ON State Leakage Current	$0V \le A, B_n \le V_{CC}$ Figure 2	1.65 to 5.5	-	±0.05	±1	-	±10	μA
I _{S(ON)}	ON State Leakage Current	-0.1V \leq A, B _n \leq V _{CC} Figure 2	1.65 to 5.5	-	±0.05	±2	-	±20	μA
I _{cc}	Quiescent Supply Current	Select = V_{CC} or GND A, Bn = V_{CC} or GND $I_{OUT} = 0$	5.5	-	1.0	10	-	40	μA
∆l _{cc}	Additional Supply Current	Select= $V_{CC} - 0.6V$ A, B _n = V_{CC} or GND I _{OUT} = 0	5.5	-	30	500	-	5,000	μA
Cı	Input Capacitance Select Pin	-	3.3	-	2.5	-	-	-	pF
$C_{S(OFF)}$	OFF State Capacitance	Select = V_{CC} or GND A, B _n = V_{CC} or GND $I_{OUT} = 0$	3.3	-	6.0	-	-	-	pF
C _{S(ON)}	ON State Capacitance	Select = V_{CC} or GND A, B _n = V_{CC} or GND $I_{OUT} = 0$	3.3	-	18	-	-	-	pF

Note: 8. Typical performance information is included in figures 11 to 34 on pages 11 to 14.





=lectrica	I Charac	teristics (All typical val	ues are at $T_J = -$	-25°C)					
		Test Condition		T,	a = -40 to +85	°C	T _A = -40	to +125°C	
Symbol Parameter		(Note 9)	V _{cc} (V)	Min	Тур	Max	Min	Max	Unit
		$V_1 = 0V, I_0 = 4mA$	1.05	-	12.5	18	-	27	
		V _I = 1.65V, I _O = -4mA	1.05	-	14	18	-	35	1
		$V_1 = 0V, I_0 = 8mA$	0.0	-	9.0	16	-	24	
		$V_1 = 2.3V, I_0 = -8mA$	2.3	-	9.0	2016	-	30	
		$V_1 = 0V, I_0 = 12mA$	27	-	8.0	14	-	21	
R _{on}	Resistance	$V_1 = 2.7V, I_0 = -12mA$	2.1	-	8.0	14	-	27	Ω
		$V_1 = 0V, I_0 = 24mA$	2.0	-	7.0	12	-	18	
		$V_1 = 3.0V, I_0 = -24mA$	3.0	-	7.0	12	-	23	
		$V_1 = 0V, I_0 = 32mA$		-	5.5	10	-	15	
		$V_1 = 2.7V, I_0 = -32mA$	4.5	-	6.0	12	-	17	1
		$V_1 = 4.5V, I_0 = -32mA$		-	5.5	10	-	15	
		$I_A = 4mA, 0 \le V_{BN} \le V_{CC}$	1.65	-	34	130	-	195	Ω
	On	$I_A = 8mA, 0 \le V_{BN} \le V_{CC}$	2.3 2.7	-	5	30	-	45	
R _{RANGE}	Over Signal	$I_A = 12mA, 0 \le V_{BN} \le V_{CC}$		-	4	25	-	38	
	Range	$I_A = 24mA, 0 \le V_{BN} \le V_{CC}$	3.0	-	7.8	20	-	30	
		$I_A = 32mA, 0 \le V_{BN} \le V_{CC}$	4.5	-	6.2	15	-	23	
		I _A = -4mA, V _{BN} = 1.15 V	1.65	-	0.25	-	-	-	
	On Resistance	$I_A = -8mA$, $V_{BN} = 1.6 V$	2.3	-	0.25	-	-	-	
ΔR_{ON}	Match Between	$I_A = -12mA$, $V_{BN} = 1.9 V$	2.7	-	0.25	-	-	-	Ω
	Channels (Note 10)	$I_A = -24mA$, $V_{BN} = 2.1$	3.0	-	0.25	-	-	-	
		$I_A = -32mA,$ $V_{BN} = 3.15$	4.5	-	025	-	-	-	
		$I_A = -4mA$, $0 \le V_{BN} \le V_{CC}$	1.65	-	26	110	-	150	
	On	$I_A = -8mA, 0 \le V_{BN} \le V_{CC}$	2.3	-	5.0	26	-	105	
R _{flat}	Resistance	$I_A = -24mA, \ 0 \le V_{BN} \le V_{CC}$	2.7	-	3.5	16	-	35	Ω
	(Note 11)	$I_A = -24mA, 0 \le V_{BN} \le V_{CC}$	3.3	-	2.0	9	-	15	1
		$I_A = -32mA, 0 \le V_{BN} \le V_{CC}$	5.0	-	1.5	4	-	8	1

9. Switch resistance test is measured per Figure 3. Note:

10. ΔR_{ON} is measured at identical V_{CC}, temperature and voltage levels.

11. Flatness is defined as the difference between the maximum and minimum of ON resistance measured at identical V_{CC} and temperature.





Switching Characteristics

Symbol	Parameter Test Condition		Vcc	T _A = -40 to +85°C			T _A = -40 to +125°C		Unit	Figure
Symbol	Farameter	Test Condition	Volts	Min	Тур	Max	Min	Max	Unit	Number
			1.65 to 1.95	-	-	2.0	-	3.0		
	Bronagation		2.3 to 2.7	-	-	1.2	-	2.0		
t _{PHL} t _{PHL}	Delay	V _I = OPEN (Note 12)	2.7	-	-	1.0	-	1.5	ns	Figure 4
121	A to B _n		3.0 to 3.6	-	-	0.8	-	1.5		
			4.5 to 5.5	-	-	0.6	-	1.0		
			1.65 to 1.95	1.0	8.7	14.0	1.0	14.0		
	Output	$V = 2 \times V$ for t	2.3 to 2.7	1.0	5.3	7.5	1.0	7.5		
t _{PZL} t _{PZH}	Enable Time	$V_1 = 2 \times V_{CC}$ for t_{PZH}	2.7	1.0	4.9	6.0	1.0	6.0	ns	Figure 4
	Switch to B _n	(Note 13)	3.0 to 3.6	0.5	4.0	5.5	0.5	5.5		
			4.5 to 5.5	0.5	3.0	4.0	0.5	4.0		
			1.65 to 1.95	2.5	6.0	8.5	2.5	8.5		
	Output	$V_1 = 2 \times V_{CC}$ for t_{PLZ} $V_1 = 0V$ for t_{PHZ} (Note 13)	2.3 to 2.7	2.0	4.4	8.2	2.0	8.2	ns	Figure 4
t _{PLZ} t _{PHZ}	Disable Time		2.7	1.5	4.2	8.0	1.5	8.0		
	Switch to Bn		3.0 to 3.6	1.5	3.6	7.8	1.5	7.8		
			4.5 to 5.5	0.8	2.9	7.5	0.8	7.5		
			1.65 to 1.95	0.5	-		0.5	-		
	Brook Boforo		2.3 to 2.7	0.5	-	-	0.5	-		
t _{B-M}	Make Time	-	2.7	0.5	-	-	0.5	-	ns	Figure 5
	(Note 9)	3.0 to 3.6	0.5		-	0.5	-			
			4.5 to 5.5	0.5	-	-	0.5			
0	Charge	$C_L = 0.1 \text{ nF},$ $V_{GEN} = 0V$	5.0	-	7.0	-	-	-		Figure 6
Q	(Note 9)	$R_{GEN} = 0 \Omega$	3.3		3.0	-	-	-	pC	Figure 6
QIRR	Off Isolation (Note 11)	$R_L = 50 \Omega$, f = 10MHz	1.65 ~ 5.5	-	-42	-	-	-	dB	Figure 7
Xtalk	Crosstalk	$R_L = 50 \ \Omega$, f = 10MHz	1.65 ~ 5.5	-	-42	-	-	-	dB	Figure 8
BW	-3dB Bandwidth	R _L = 50 Ω	1.65 ~ 5.5	-	300	-	-	-	MHz	Figure 9
THD	Total Harmonic Distortion (Note 9)	R_L = 600 Ω, 0.5 V _{P-P} , f = 600Hz to 20kHz	5.0	-	0.1	-	-	-	%	Figure 10

12. Due to the symmetry of the part, the direction of the propagation delay applies to either direction A to B_n or B_n to A. Propagation time is the calculated RC time constant of the typical ON resistance of the switch and the specified load capacitance when capacitance when driven by Notes: an ideal voltage source. 13. The Switch signal enable and disables time are the same for Bn and A if they are reversed at input and output.





Parameter Measurement Information



Condition 1: $V_I = GND, V_O = V_{CC}$ Condition 2: $V_I = V_{CC}, V_O = GND$





Figure 2 ON –State Leakage Curent Test



Figure 3 ON State Resistance Test





Parameter Measurement Information (Notes 15-19)



TEST	S1	RL
t _{PLH} /t _{PHL}	Open	500Ω
t _{PLZ} /t _{PZL}	Vload	500Ω
t _{PHZ} /t _{PZH}	GND	500Ω

v	Inputs				C∟	MA
VCC	VI	t _r /t _f	VM	VLOAD	(Note 14)	VΔ
1.8V ± 0.15V	V _{CC}	≤2ns	V _{CC} /2	2 x V _{CC}	50pF	0.1V
2.5V ± 0.2V	V _{CC}	≤2ns	V _{CC} /2	$2 \times V_{CC}$	50pF	0.1V
3.3V ± 0.3V	Vcc	≤2.5ns	V _{CC} /2	2 x V _{CC}	50pF	0.1V
5V ± 0.5V	Vcc	≤2.5ns	V _{cc} /2	2 x V _{CC}	50pF	0.1V





Voltage Waveform Propagation Delay Times



Figure 4 Load Circuit and Voltage Waveforms

Notes:

14. Includes test lead and test apparatus capacitance.
 15. All pulses are supplied at pulse repetition rate ≤ 10MHz.
 16. Inputs are measured separately one transition per measurement.

17. tPLZ and tPHZ are the same as tdis.

18. tPZL and tPZH are the same as tEN.

19. t_{PLH} and t_{PHL} are the same as $t_{PD.}$





Parameter Measurement Information (Continued)







B1 2 ξ RL Α GND 50Ω ş tin -1 RL=50Ω

Figure 7 OFF Isolation





Parameter Measurement Information (Cont.)







Adjust fin voltage to obtain 0 dBm level at input. Adjust fin frequency until dB meter reads -3 dB.

Figure 9 Bandwdith









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Typical Performance Characteristics















Figure 12 ON state Resistance Vcc = 1.8 V; I_{Bn} = 4ma







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Typical Performance Characteristics (Continued)



Figure 17 ON state Resistance Vcc = 3.3 V; I_{Bn} = 24ma



Figure 19 ON state Resistance Vcc = 5.5 V; I_{Bn} = 32ma



Figure 21 I_{S(OFF)} OFF state leakage V_{IN} = 0 V







Figure 20 Ann-Resistance Match Between Channels







Typical Performance Characteristics (Cont.)









Figure 27 I_{cc} verses Temperture



Figure 24 $I_{S(ON)}$ ON state leakage $V_{IN} = 0$ V



Figure 26 $I_{S(ON)}$ ON state leakage $V_{IN} = -0.2V$



Figure 28 Delta Icc verses Temperture





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Typical Performance Characteristics (Cont.)







Figure 31 V_{IH}, V_{IL}, Hysteresis V_{CC} = 3 V and V_{CC}= 3.3 V



Figure 30 V $_{\text{IH}},$ V $_{\text{IL}},$ Hysteresis V $_{\text{CC}}$ = 2.3 V and V $_{\text{CC}}$ = 2.7 V



Figure 32 V_{IH}, V_{IL}, Hysteresis V_{CC} = 4.5 V and V_{CC}= 5.5 V





Marking Information

(1) SOT363



Part Number	Package	Identification Code		
74LVC1G3157DW	SOT363	J7		

(2) X2-DFN1410-6



 $\begin{array}{c} \underline{XX}: \text{ Identification Code} \\ \underline{Y}: \ \text{Year } 0 - 9 \\ \underline{W}: \ \text{Week}: A - Z: 1 - 26 \ \text{week}; \\ a - z: 27 - 52 \ \text{week}; \\ z \ \text{represents } 52 \ \text{and } 53 \ \text{week} \\ \underline{X}: A - Z: \ \text{Internal Code} \end{array}$

Part Number	Package	Identification Code		
74LVC1G3157FZ4	X2-DFN1410-6	J7		

Package Characteristics (All typical values are at $V_{CC} = 3.3V$, $T_A = +25^{\circ}C$)

Symbol	Parameter	Test Conditions	V _{cc}	Min	Тур.	Max	Unit
θ_{JA}	Thermal Resistance	SOT363	(Note 20)	-	371	-	°C/W
	Junction-to-Ambient	X2-DFN1410-6		-	460	-	
θ _{JC}	Thermal Resistance	SOT363	(Note 20)	-	143	-	°C/W
	Junction-to-Case	X2-DFN1410-6		-	265	-	

Note: 20. Test condition SOT363, and X2-DFN1410-6: Device mounted on FR-4 substrate PC board, 2oz. copper, with minimum recommended pad layout.





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SOT363 Package Outline Dimensions and Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.





	SOT363				
Dim	Min	Max	Тур		
A1	0.00	0.10	0.05		
A2	0.90	1.00	1.00		
b	0.10	0.30	0.25		
С	0.10	0.22	0.11		
D	1.80	2.20	2.15		
E	2.00	2.20	2.10		
E1	1.15	1.35	1.30		
е	0.650 BSC				
F	0.40	0.45	0.425		
L	0.25	0.40	0.30		
а	0°	8°			
All Dimensions in mm					



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Ŷ	0.600
Y1	2.500





X2-DFN1410-6 Package Outline Dimensions and Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



V2 DEN1440 6				
AZ-DFN1410-0				
Dim	Min	n Max Ty		
Α		0.40	0.39	
A1	0.00	0.05	0.02	
A3	_	_	0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
E	0.95	1.05	1.00	
е	_	_	0.50	
L	0.25	0.35	0.30	
Z			0.10	
Z1	0.045	0.105	0.075	
All Dimensions in mm				



Dimonsions	Value	
Dimensions	(in mm)	
С	0.500	
G	0.250	
Х	0.250	
X1	1.250	
Y	0.525	
Y1	1.250	





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